

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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PCT International Application No. : PCT/DE03/004036

VERIFICATION OF A TRANSLATION

I, Charles Edward SITCH BA,  
Deputy Managing Director of RWS Group Ltd, of Europa House, Marham Way, Gerrards  
Cross, Buckinghamshire, England declare:

That the translator responsible for the attached translation is knowledgeable in the German  
language in which the below identified international application was filed, and that, to the  
best of RWS Group Ltd knowledge and belief, the English translation of the amended sheet  
of the international application No. PCT/DE03/004036 is a true and complete translation of  
the amended sheet of the above identified international application as filed.

I hereby declare that all the statements made herein of my own knowledge are true and that all  
statements made on information and belief are believed to be true; and further that these  
statements were made with the knowledge that willful false statements and the like so made  
are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United  
States Code and that such willful false statements may jeopardize the validity of the patent  
application issued thereon.

Date: June 30, 2005

Signature :



For and on behalf of RWS Group Ltd

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England.

**New patent claim 1:**

An organic field effect transistor (OFET), which  
5 comprises at least a first electrode layer having  
source and drain electrodes (1, 2 and 5, 7), a  
semiconducting layer, an insulator layer and a second  
electrode layer (8 and 13), and in which one of the  
10 electrodes (source or drain) in the first electrode  
layer surrounds the respective other electrode in a  
two-dimensional manner with the exception of one side  
or location (the connection side or location) of this  
electrode,  
characterized in that  
15 a u-shaped and/or meandering current channel (3, 6),  
which begins and ends on one side of an electrode of  
the first electrode layer, can be formed in the  
semiconducting layer.

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**Neuer Patentanspruch 1:**

Organischer Feldeffekttransistor (OFET), zumindest eine erste Elektrodenschicht mit Source- und Drain-Elektroden (1,2 und 5,7), eine halbleitende Schicht, eine Isolatorschicht und eine zweite Elektrodenschicht (8 und 13) umfassend, bei dem in der ersten Elektrodenschicht eine der Elektroden, Source oder Drain die jeweils andere bis auf eine Seite oder Stelle, die Anschlussseite oder -stelle dieser Elektrode, 2-dimensional umschließt, dadurch gekennzeichnet, dass ein u- und/oder mäanderförmiger Stromkanal (3,6) in der halbleitenden Schicht ausbildbar ist, der an einer Seite einer Elektrode der ersten Elektrodenschicht beginnt und endet.